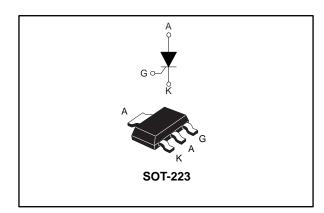
P0102MN



Sensitive 0.8 A SCR thyristor

Datasheet - production data

www.st.com



Features

- I_{T(RMS)} 0.8 A
- 125 °C max T_i
- Low 0.2 mA gate current
- 600 V V_{DRM}/V_{RRM}
- ECOPACK®2 compliant component

Applications

- Proximity sensors
- Gate driver for large thyristors
- Overvoltage crowbar protection
- Ground fault circuit interrupters
- Arc fault circuit interrupter
- Standby mode power supplies

This is information on a product in full production.

Residual current detector

Description

Thanks to highly sensitive triggering levels, the 0.8 A P0102MN SCR thyristor is suitable for all applications where available gate current is limited. This device offers a high blocking voltage of 600 V, ideal for applications like interrupters circuits.

The surface mount SOT-223 package allows compact, SMD based designs for automated manufacturing.

Table 1: Device summary

| Symbol | Value | Unit |
|------------------------------------|-------|------|
| I _{T(RMS)} | 0.8 | Α |
| V _{DRM} /V _{RRM} | 600 | V |
| lgт | 0.2 | mA |
| T _j max. | 125 | °C |

Characteristics P0102MN

1 Characteristics

Table 2: Absolute maximum ratings (limiting values), $T_j = 25$ °C unless otherwise specified

| Symbol | Parameter | Value | Unit | | |
|------------------------------------|---|-------------|--------------------------|-------------|------------------|
| I _{T(RMS)} | RMS on-state current (180 ° conduction | n angle) | T . 70 °C | 0.8 | ^ |
| I _{T(AV)} | Average on-state current (180 ° conduc | tion angle) | T _{amb} = 70 °C | 0.5 | Α |
| l | Non repetitive surge peak on-state current $t_p = 8.3 \text{ ms}$ $(T_j \text{ initial} = 25 \text{ °C})$ $t_p = 10 \text{ ms}$ | | $t_p = 8.3 \text{ ms}$ | 8 | ۸ |
| ITSM | | | $t_p = 10 \text{ ms}$ | 7 | Α |
| l ² t | I ² t value for fusing | | $t_p = 10 \text{ ms}$ | 0.24 | A ² s |
| dl/dt | Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$ $f = 60 \text{ Hz}$ | | T _j = 125 °C | 50 | A/µs |
| V _{DRM} /V _{RRM} | Repetitive peak off-state voltage | | T _j = 125 °C | 600 | V |
| I _{GM} | Peak gate current $t_p = 20 \mu s$ | | T _j = 125 °C | 1 | Α |
| P _{G(AV)} | Average gate power dissipation | 0.1 | W | | |
| T _{stg} | Storage junction temperature range | | | -40 to +150 | °C |
| T _j | Operating junction temperature | | | -40 to +125 | °C |

Table 3: Electrical characteristics ($T_j = 25$ °C unless otherwise specified)

| Symbol | Test conditions | | Value | Unit | |
|------------------|--|------|-------|------|----------|
| lgт | V 40V B 440 0 | | Max. | 200 | μΑ |
| V _G T | $V_D = 12 \text{ V}, R_L = 140 \Omega$ | | Max. | 0.8 | V |
| V_{GD} | $V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, R_{GK} = 1000 \Omega$ | Min. | 0.1 | ٧ | |
| V_{RG} | I _{RG} = 10 μA | Min. | 8 | V | |
| lμ | $I_T = 50 \text{ mA}, R_{GK} = 1000 \Omega$ | Max. | 5 | mA | |
| IL | I_G = 1 mA, R_{GK} = 1000 Ω | | Max. | 6 | mA |
| dV/dt | $V_D = 67 \% V_{DRM}, R_{GK} = 1000 \Omega$ $T_j = 125 °C$ | | Min. | 75 | V/µs |

Table 4: Static characteristics

| Symbol | Test condition | Value | Unit | | |
|------------------------------------|--|-------------------------|------|------|----|
| V _{TM} | $I_{TM} = 1.6 \text{ A}, t_p = 380 \ \mu \text{s}$ | T _j = 25 °C | Max. | 1.95 | V |
| Vто | Threshold voltage | T _j = 125 °C | Max. | 0.95 | V |
| R _D | Dynamic resistance | T _j = 125 °C | Max. | 600 | mΩ |
| 1 // | V V V P 4000 0 | T _j = 25 °C | Max | 10 | |
| I _{DRM} /I _{RRM} | IDRM/IRRM $V_D = V_{DRM}$; $V_R = V_{RRM}$, $R_{GK} = 1000 \Omega$ | | Max. | 100 | μΑ |

Table 5: Thermal parameters

| Symbol | Parameter | Value | Unit | |
|----------------------|--------------------------|----------------------------|------|------|
| R _{th(j-t)} | Junction to tab (DC) | | 30 | 0044 |
| $R_{th(j-a)}$ | Junction to ambient (DC) | $S^{(1)} = 5 \text{ cm}^2$ | 60 | °C/W |

Notes:

⁽¹⁾S = copper surface under tab.

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P0102MN Characteristics

360°

1.1 Characteristics (curves)

0.6

0.5

0.3

Figure 1: Maximum average power dissipation versus average on-state current

P(W)

1.0

0.9

0.8

0.7

case temperature $I_{T(AV)}(A)$ 1.1 D.C. (SOT-223) 1.0 0.9 0.8 0.7 0.6 0.5 0.4 0.3 0.2 0.1 T_{lead} (°C) 0.0 0 25 50 100 125

Figure 2: Average and DC on-state current versus

0.2 0.1 0.0 0.0 0.1 0.2 0.3 0.4 0.5 0.6

Figure 3: Average and DC on-state current versus ambient temperature

 $I_{T(AV)}(A)$ 1.2 1.1 1.0 0.9 0.8 0.7 0.6 0.5 0.4 0.3 0.2 0.1 T_{amb}(°C) 0.0 50

Figure 4: Relative variation of thermal impedance versus pulse duration

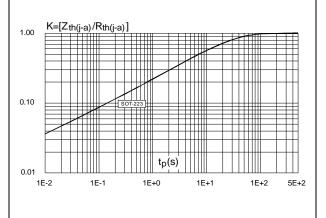


Figure 5: Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

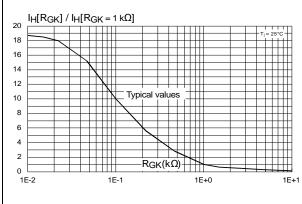
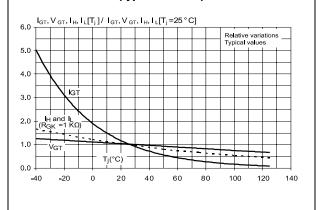


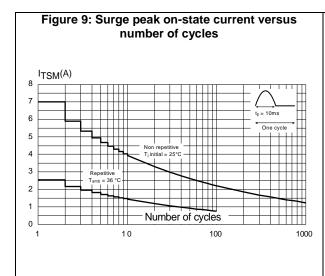
Figure 6: Relative variation of holding and latching current versus junction temperature (typical values)

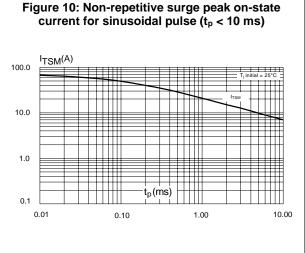


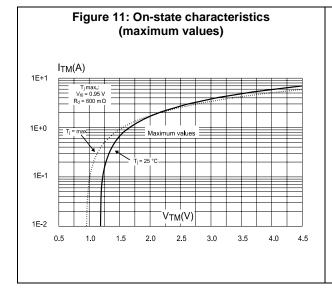


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Figure 7: Relative variation of static dV/dt immunity versus gate-cathode resistance (typical values) $dV/dt[R_{GK}] / dV/dt[R_{GK} = 1k\Omega]$ 10.0 Typical values $R_{GK}(k\Omega)$ 0.1 0.2 0.4 0.6 0.8 1.0 1.2 1.6 1.8 2.0







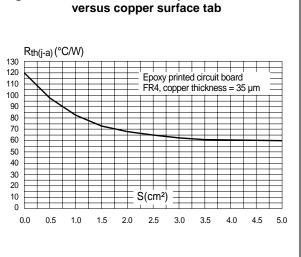


Figure 12: Thermal resistance junction to ambient

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P0102MN Package information

2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Lead-free package
- Halogen free molding resin
- Epoxy meets UL94, V0

2.1 SOT-223 package information

Figure 13: SOT-223 package outline

D
B1

Outline

Outlin



Table 6: SOT-223 package mechanical data

| Dim. | | Millimeters Inches ⁽¹⁾ | | | | |
|------------------|------|-----------------------------------|------|--------|--------|--------|
| DIM. | Min. | Тур. | Max. | Min. | Тур. | Max. |
| А | | | 1.8 | | | 0.0709 |
| A1 | 0.02 | | 0.1 | 0.0008 | | 0.0039 |
| В | 0.6 | 0.7 | 0.85 | 0.0236 | 0.0276 | 0.0335 |
| B1 | 2.9 | 3 | 3.15 | 0.1142 | 0.1181 | 0.1240 |
| С | 0.24 | 0.26 | 0.35 | 0.0094 | 0.0102 | 0.0138 |
| D ⁽²⁾ | 6.3 | 6.5 | 6.7 | 0.2480 | 0.2559 | 0.2638 |
| е | | 2.3 | | | 0.0906 | |
| e1 | | 4.6 | | | 0.1811 | |
| E | 3.3 | 3.5 | 3.7 | 0.1299 | 0.1378 | 0.1457 |
| Н | 6.7 | 7.0 | 7.3 | 0.2638 | 0.2756 | 0.2874 |
| V | | | 10° | | | 10° |

Notes:

3.3 6.4 (3x) 1.5 4.6 0046067

Figure 14: SOT-223 recommended footprint (dimensions are in mm)

 $^{^{(1)}}$ Inches dimensions given only for reference

 $^{^{(2)}}$ Does not include mold flash or protusions. Mold flash or protusions must not exceed 0.15 mm (0.006 inches)

P0102MN Ordering information

3 Ordering information

Figure 15: Ordering information scheme

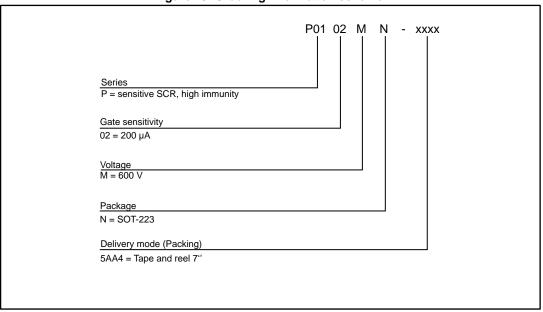


Table 7: Ordering information

| Order code | Marking | Package | Weight | Base qty. | Delivery mode |
|--------------|---------|---------|--------|-----------|------------------|
| P0102MN 5AA4 | P2M | SOT-223 | 0.12 g | 1000 | Tape and reel 7" |

4 Revision history

Table 8: Document revision history

| Date | Revision | Changes |
|-------------|----------|------------------|
| 06-Oct-2017 | 1 | Initial release. |



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